PCN Number: 20160331001 B			F	PCN Da	te: Aug 2	5, 2017		
Title:	Qualification of CFAB as an additional wafer fab site option for select devices in LBC5 process technology						_BC5	
Customer	Contact:	PCN	Manager		Dept:	Quality Services		ices
Proposed	1 st Ship Date		82016	Estimated Availability	l Sample		Date prov sample re	ided at
Change Ty	/pe:				, -			-10.000
	bly Site		Assembly P	rocess		Assen	nbly Materia	ls
Design			Electrical S				anical Specif	
Test S				ipping/Labelii	ng 🔲		Process	reaction
=	Bump Site		Wafer Bum				r Bump Proc	ess
	Fab Site		Wafer Fab I				r Fab Proces	
Valci	Tub Site		Part numbe			Walci	T db T Toccs	3
				l Details				
Description	n of Change:	_	PCN	Details				
Description	in or change							
are identified with a strikethrough and are highlighted in yellow in the Product Affected Section. These devices will remain at the current wafer fab site at DP1DM5. This change notification is to announce the qualification of CFAB as an additional wafer fab site option for the LBC5 devices listed in the product affected section of this document.								
	Curre	ent			Addition	al		
Current I		cess			Wafer			
Site	rab Pio	CESS	Diameter	Additional Fab Site	Proces		Warer Diameter	
DP1DM	5 I.F	3C5	200 mm	CFAB	LBC5		200 mm	
Reason fo	The LBC5 process technology has been running successfully in production at CFAB since 2012. Reason for Change:							
Continuity	of Supply							
Anticipate	ed impact on	Form, F	it, Function,	Quality or R	eliability (p	ositive	e / negativ	e):
None	-							
	o product ide	ontificat	ion resulting	from this D	CN:			
	o product ide	Entineat	ion resulting	HOIII UIIS P	CIV.			
Current	Chin Site Origin Code Chin Site Country		Cł	nip Site City				
DP	1DM5		DM5		SA		Dallas	
New								
	p Site	Chip Sit	te Origin Code (20L)	Chip Site Country Code (21L)		nip Site City		
CFAB			CU3 CH				Chengdu	
	1 10			<u>.</u>			Chenguu	

Sample product shipping label (not actual product label)

TEXAS INSTRUMENTS MADE IN: Malaysia 2DC: 20: G4

(1P) \$N74L\$07N\$R (Q) 2000 (D) 0336 (31T)LOT: 3959047MLA (4W) TKY(1T) 7523483\$I2 (P) (2P) REV: (V) 0033317

(26) REV: (20L) CSO: SHE (22L) ASO: HLA (23L) AGO: MYS

2DC: 20: MSL '2 /260C/1 YEAR SEAL DT MSL 1 /235C/UNLIM 03/29/04

OPT: ITEM: IDI: EA

L: 5A (L)T0:1750

Product Affected:

Product Affected:	Product Affected:				
CXD9981TNDDV	TAS5342LAADDVR	TAS5614ADKD	TAS5708PHPR		
CXD9981TNDDVR	TAS5352ADDV	TAS5614ADKDR	TAS5710PHP		
CXD9981UTNDDV	TAS5352ADDVR	TAS5614APHD	TAS5710PHPR		
CXD9981UTNDDVR	TAS5613ADKD	TAS5614APHDR	TPA3251D2DDV		
TAS5342ADDV	TAS5613ADKDR	TAS5708LPHP	TPA3251D2DDVR		
TAS5342ADDVR	TAS5613APHD	TAS5708LPHPR	TPS65149RSHR		
TAS5342LAADDV	TAS5613APHDR	TAS5708PHP	TPS65155RKPR		

Qualification Report

Qualification of LBC5 Process Technology at CFAB Approved 03/02/2012

Die Attributes

Attributes	Process QBS: TAS5613APHD Approved: 3/2/2012	Process QBS: DRV8813A0PWP Approved: 3/2/2012	Process QBS: SN8C0183PWP Approved: 3/2/2012
Wafer Fab Site	CFAB	CFAB	CFAB
Wafer Fab Process	LBC5	LBC5	LBC5
Wafer Diameter	200mm	200mm	200mm

⁻ QBS: Qual By Similarity

Qualification Results Data Displayed as: Number of lots / Total sample size / Total failed

Туре	Test Name / Condition	Duration	Qual Device: TAS5613APHD	Qual Device: DRV8813A0PWP	Qual Device: SN8C0183PWP
AC	Autoclave 121C	96 Hours	3/77/0	3/77/0	-
ED	Electrical Characterization	Per Datasheet	3/Pass	3/Pass	3/3/0

⁻ Qual Device TAS5613APHD and SN8C0183PWP are qualified at LEVEL3-260C

⁻ Qual Device DRV8813A0PWP is qualified at LEVEL1-260C

		Parameters			
	Biased HAST,				
HAST	130C/85%RH	96 Hours	3/77/0	-	-
HBM	ESD - HBM	1500 V	3/21/0	1/3/0	-
CDM	ESD - CDM	250 V	3/15/0	1/3/0	-
HTOL	Life Test, 155C	240 Hours	3/77/0		3/77/0
	High Temp Storage Bake				
HTSL	170C	420 Hours	3/77/0	-	-
LU	Latch-up	(per JESD78)	3/6/0	1/6/0	-
TC	Temperature Cycle, -65/150C	500 Cycles	3/77/0	3/77/0	-

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
- The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7 eV: 150 C/1 k Hours, and 170 C/420 Hours
- The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles Quality and Environmental data is available at TI's external Web site: http://www.ti.com/ **Green/Pb-free Status:**

Qualified Pb-Free(SMT) and Green

For questions regarding this notice, e-mails can be sent to the regional contacts shown below, or you can contact your local Field Sales Representative.

Location	E-Mail
USA	PCNAmericasContact@list.ti.com
Europe	PCNEuropeContact@list.ti.com
Asia Pacific	PCNAsiaContact@list.ti.com
Japan	PCNJapanContact@list.ti.com